Preferred Device

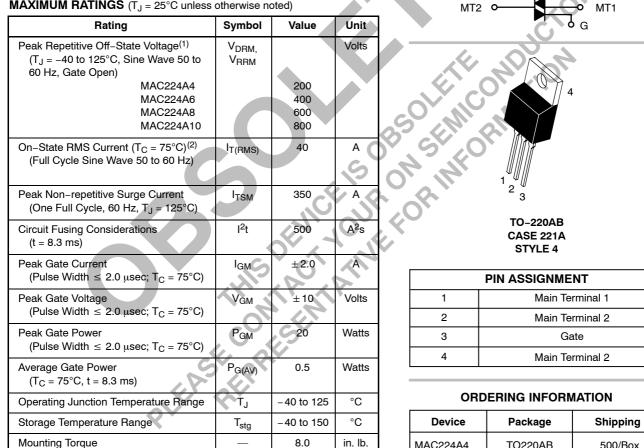
Triacs

Silicon Bidirectional Thyristors

Designed primarily for full-wave ac control applications such as lighting systems, heater controls, motor controls and power supplies.

- Blocking Voltage to 800 Volts
- All Diffused and Glass-Passivated Junctions for Parameter Uniformity and Stability
- Gate Triggering Guaranteed in Four Modes
- High Current and Surge Ratings
- Device Marking: Logo, Device Type, e.g., MAC224A4, Date Code

MAXIMUM RATINGS (T_{.1} = 25°C unless otherwise noted)



(1) V_{DRM}, V_{RRM} for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

(2) This device is rated for use in applications subject to high surge conditions. Care must be taken to insure proper heat sinking when the device is to be used at high sustained currents. (See Figure 1 for maximum case temperatures.)



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TRIACS **40 AMPERES RMS** 200 thru 800 VOLTS

PIN ASSIGNMENT			
1	Main Terminal 1		
2	Main Terminal 2		
3	Gate		
4	Main Terminal 2		

Device	Package	Shipping
MAC224A4	TO220AB	500/Box
MAC224A6	TO220AB	500/Box
MAC224A8	TO220AB	500/Box
MAC224A10	TO220AB	500/Box

Preferred devices are recommended choices for future use and best overall value.

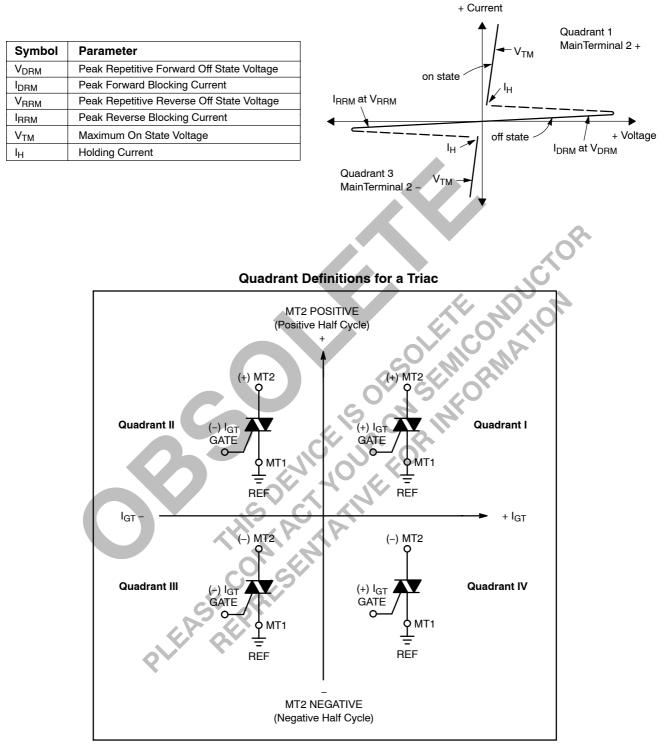
THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance — Junction to Case — Junction to Ambient	R _{θJC} R _{θJA}	1.0 60	°C/W
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds	ΤL	260	°C

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted; Electricals apply in both directions)

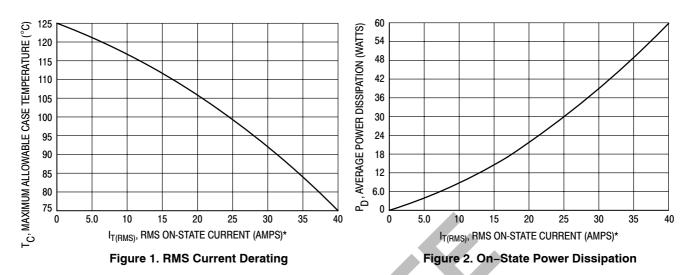
Characteristic	Symbol	Min	Тур	Max	Unit
DFF CHARACTERISTICS			•	•	
$\label{eq:peak Repetitive Blocking Current} \begin{array}{l} \mbox{(Rated V}_{DRM}, \mbox{V}_{RRM}; \mbox{Gate Open}) & T_J = 25^{\circ}\mbox{C} \\ T_J = 125^{\circ}\mbox{C} \end{array}$	I _{DRM,} I _{RRM}			10 2.0	μA mA
DN CHARACTERISTICS					
Peak On–State Voltage ($I_{TM} = \pm 56$ A Peak, Pulse Width \leq 2 ms, Duty Cycle \leq 2%)	V _{TM}	-	1.4	1.85	Volts
Gate Trigger Current (Continuous dc) $(V_D = 12 V, R_L = 100 \Omega)$ MT2(+), G(+); MT2(+), G(-); MT2(+), G(-) MT2(-), G(+)	I _{GT}	_	25 40	50 75	mA
Gate Trigger Voltage (Continuous dc) $(V_D = 12 V, R_L = 100 \Omega)$ MT2(+), G(+); MT2(-), G(-); MT(+), G(-) MT2(-), G(+)	V _{GT}	Ę	1.1	2.0 2.5	Volts
Gate Non-Trigger Voltage (V_D = 12 V, T_J = 125°C, R_L = 100 Ω) All Quadrants	V _{GD}	0.2	-		Volts
Holding Current (V_D = 12 Vdc, Gate Open, Initiating Current = ±200 mA)		_	30	75	mA
Gate Controlled Turn-On Time (V_D = Rated V_{DRM} , I_{TM} = 56 A Peak, I_G = 200 mA)	tgt	_	1.5	_	μs
VYNAMIC CHARACTERISTICS	4				
Critical Rate of Rise of Off-State Voltage (V_D = Rated V_{DRM} , Exponential Waveform, T_C = 125°C)	dv/dt	_	50	—	V/µs
Critical Rate of Rise of Commutation Voltage (V_D = Rated V_{DRM} , I_{TM} = 56 A Peak, Commutating di/dt = 20.2 A/ms, Gate Unenergized, T_C = 75°C)	dv/dt(c)	-	5.0	_	V/µs
di/dt = 20.2 A/ms, Gate Unenergized, T _C = 75°C)					

Voltage Current Characteristic of Triacs (Bidirectional Device)

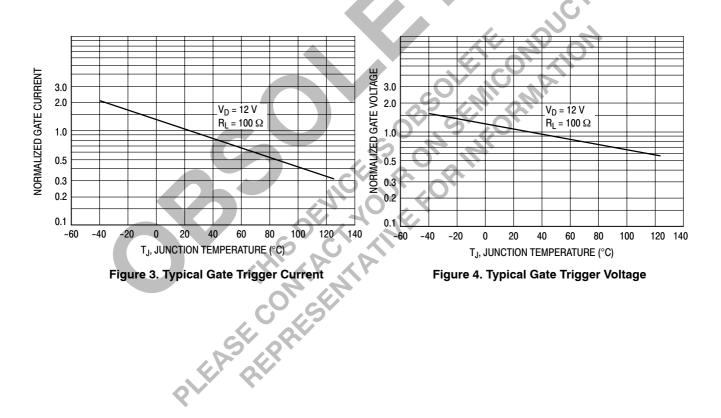


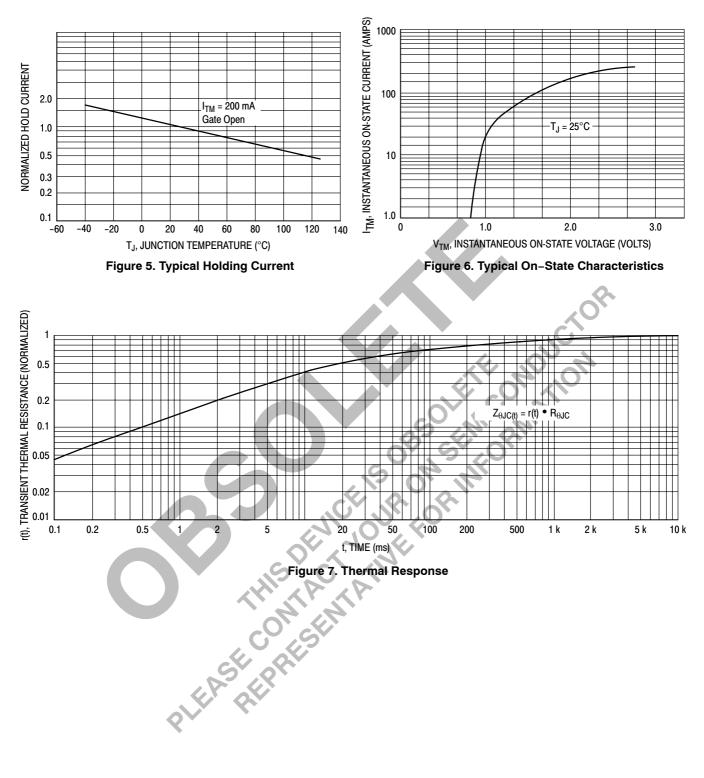
All polarities are referenced to MT1.

With in-phase signals (using standard AC lines) quadrants I and III are used.



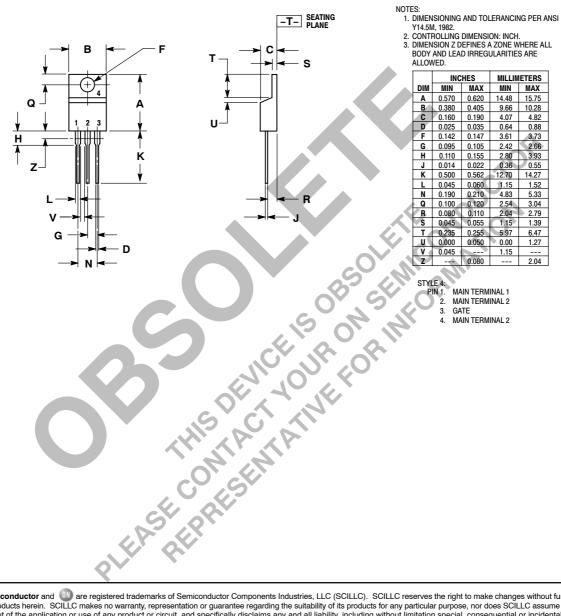
*This device is rated for use in applications subject to high surge conditions. Care must be taken to insure proper heat sinking when the device is to be used at high sustained currents.





PACKAGE DIMENSIONS

TO-220AB CASE 221A-07 ISSUE Z



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